# **MOSFET** – Power, N-Channel, Logic Level, DPAK

# 18 A, 60 V

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

#### **Features**

- AEC Q101 Qualified NTDV18N06L
- These Devices are Pb-Free and are RoHS Compliant

#### **Typical Applications**

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

# MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	60	Vdc
Drain-to-Gate Voltage (R <sub>GS</sub> = 10 MΩ)	$V_{DGR}$	60	Vdc
Gate-to-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤10 ms)	V <sub>GS</sub> V <sub>GS</sub>	±15 ±20	Vdc
Drain Current  - Continuous @ $T_A = 25^{\circ}C$ - Continuous @ $T_A = 100^{\circ}C$ - Single Pulse $(t_p \le 10 \ \mu s)$	I <sub>D</sub> I <sub>D</sub> I <sub>DM</sub>	18 10 54	Adc Apk
Total Power Dissipation @ T <sub>A</sub> = 25°C  Derate above 25°C  Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 2)	P <sub>D</sub>	55 0.36 2.1	W W/°C W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^{\circ}\text{C}$ ( $V_{DD} = 50 \text{ Vdc}, V_{GS} = 5.0 \text{ Vdc},$ $L = 1.0 \text{ mH}, I_L(\text{pk}) = 12 \text{ A}, V_{DS} = 60 \text{ Vdc})$	E <sub>AS</sub>	72	mJ
Thermal Resistance  - Junction-to-Case  - Junction-to-Ambient (Note 1)  - Junction-to-Ambient (Note 2)	$egin{array}{c} R_{ heta JC} \ R_{ heta JA} \ R_{ heta JA} \end{array}$	2.73 100 71.4	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

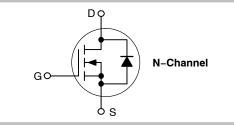
- When surface mounted to an FR-4 board using the minimum recommended pad size
- 2. When surface mounted to an FR-4 board using the 0.5 sq in drain pad size.



## ON Semiconductor®

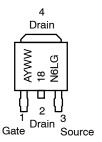
#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
60 V	54 mΩ@5.0 V	18 A (Note 1)





# MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location\* 18N6L = Device Code

Y = Year
WW = Work Week
G = Pb-Free Device

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 3) $(V_{GS}=0\ Vdc,\ I_D=250\ \mu Adc)$ Temperature Coefficient (Positive)			60 -	70 57.6	- -	Vdc mV/°C
Zero Gate Voltage Drain Current $(V_{DS} = 60 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$ $(V_{DS} = 60 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, T_J = 150^{\circ}\text{C})$			- -	- -	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>G</sub>	<sub>IS</sub> = ±15 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	_	-	±100	nAdc
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage (Note 3) $(V_{DS} = V_{GS},  I_D = 250 \; \mu Adc)$ Threshold Temperature Coefficie	· · · · ·	V <sub>GS(th)</sub>	1.0	1.8 5.2	2.0 -	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 3) $(V_{GS} = 5.0 \text{ Vdc}, I_D = 9.0 \text{ Adc})$			-	54	65	mΩ
Static Drain-to-Source On-Resistance (Note 3) $(V_{GS} = 5.0 \text{ Vdc}, I_D = 18 \text{ Adc})$ $(V_{GS} = 5.0 \text{ Vdc}, I_D = 9.0 \text{ Adc}, T_J = 150^{\circ}\text{C})$			-	1.0 0.86	1.3 -	Vdc
Forward Transconductance (Note	9 <sub>FS</sub>	-	13.5	-	mhos	
YNAMIC CHARACTERISTICS						
Input Capacitance	05)/4- // 05/4-	C <sub>iss</sub>	-	482	675	pF
Output Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>oss</sub>	-	166	230	
Transfer Capacitance	1 = 1.3 1.11.12)	C <sub>rss</sub>	-	56	80	
WITCHING CHARACTERISTICS	(Note 4)					
Turn-On Delay Time	00 1/1-1-40 1/1-	t <sub>d(on)</sub>	-	9.9	20	ns
Rise Time	$(V_{DD} = 30 \text{ Vdc}, I_D = 18 \text{ Adc}, V_{GS} = 5.0 \text{ Vdc},$	t <sub>r</sub>	-	79	160	
Turn-Off Delay Time	$R_G = 9.1 \Omega$ (Note 3)	t <sub>d(off)</sub>	-	19	40	
Fall Time		t <sub>f</sub>	-	38	80	
Gate Charge	(V <sub>DS</sub> = 48 Vdc, I <sub>D</sub> = 18 Adc,	Q <sub>T</sub>	-	11	22	nC
	$V_{GS} = 40 \text{ Vdc}, 10 = 10 \text{ Adc},$ $V_{GS} = 5.0 \text{ Vdc}) \text{ (Note 3)}$	Q <sub>1</sub>	-	3.2	_	
		$Q_2$	-	6.5	-	
OURCE-DRAIN DIODE CHARA		•			_	_
Forward On-Voltage	$(I_S = 18 \text{ Adc}, V_{GS} = 0 \text{ Vdc}) \text{ (Note 3)}$ $(I_S = 18 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	V <sub>SD</sub>	-	0.94 0.83	1.15 –	Vdc
Reverse Recovery Time	(1 10 Ado )/ 0 )/-	t <sub>rr</sub>	_	41	-	ns
	(I <sub>S</sub> = 18 Adc, V <sub>GS</sub> = 0 Vdc, dI <sub>S</sub> /dt = 100 A/μs) (Note 3)	ta	-	26	-	
	415/4t = 100 Fyfus) (110to 0)	t <sub>b</sub>	_	15	_	<u> </u>
Reverse Recovery Stored Charg	e	$Q_{RR}$	-	0.057	-	μС

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTD18N06LT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTDV18N06LT4G	DPAK (Pb-Free)	2500 / Tape & Reel
STD18N06LT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>3.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

<sup>4.</sup> Switching characteristics are independent of operating junction temperatures.

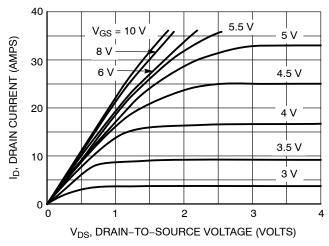


Figure 1. On-Region Characteristics

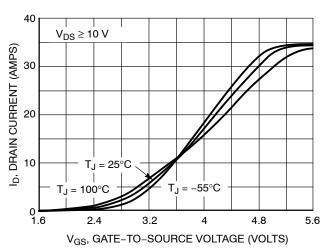


Figure 2. Transfer Characteristics

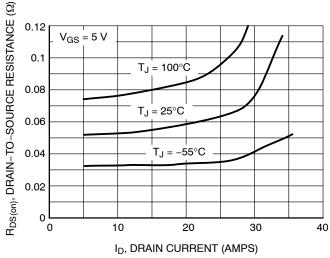


Figure 3. On–Resistance versus Gate–to–Source Voltage

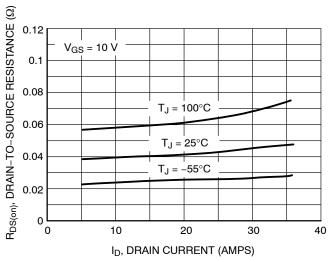


Figure 4. On-Resistance versus Drain Current and Gate Voltage

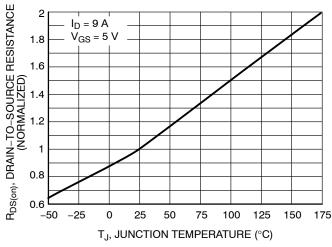


Figure 5. On–Resistance Variation with Temperature

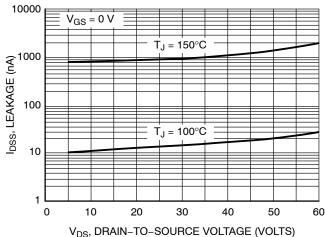


Figure 6. Drain-to-Source Leakage Current versus Voltage

#### **POWER MOSFET SWITCHING**

Switching behavior is most easily modeled and predicted by recognizing that the power MOSFET is charge controlled. The lengths of various switching intervals ( $\Delta t$ ) are determined by how fast the FET input capacitance can be charged by current from the generator.

The published capacitance data is difficult to use for calculating rise and fall because drain–gate capacitance varies greatly with applied voltage. Accordingly, gate charge data is used. In most cases, a satisfactory estimate of average input current ( $I_{G(AV)}$ ) can be made from a rudimentary analysis of the drive circuit so that

$$t = Q/I_{G(AV)}$$

During the rise and fall time interval when switching a resistive load,  $V_{GS}$  remains virtually constant at a level known as the plateau voltage,  $V_{SGP}$  Therefore, rise and fall times may be approximated by the following:

$$t_r = Q_2 x R_G/(V_{GG} - V_{GSP})$$
  
$$t_f = Q_2 x R_G/V_{GSP}$$

where

 $V_{GG}$  = the gate drive voltage, which varies from zero to  $V_{GG}$  $R_G$  = the gate drive resistance

and Q<sub>2</sub> and V<sub>GSP</sub> are read from the gate charge curve.

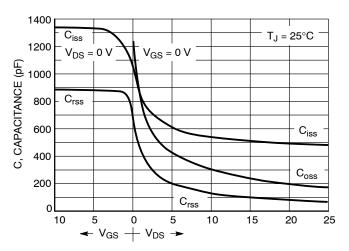
During the turn-on and turn-off delay times, gate current is not constant. The simplest calculation uses appropriate values from the capacitance curves in a standard equation for voltage change in an RC network. The equations are:

$$t_{d(on)} = R_G C_{iss} In \left[ V_{GG} / (V_{GG} - V_{GSP}) \right]$$
  
$$t_{d(off)} = R_G C_{iss} In \left( V_{GG} / V_{GSP} \right)$$

The capacitance ( $C_{iss}$ ) is read from the capacitance curve at a voltage corresponding to the off-state condition when calculating  $t_{d(on)}$  and is read at a voltage corresponding to the on-state when calculating  $t_{d(off)}$ .

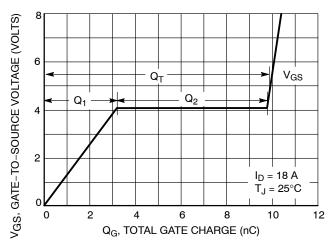
At high switching speeds, parasitic circuit elements complicate the analysis. The inductance of the MOSFET source lead, inside the package and in the circuit wiring which is common to both the drain and gate current paths, produces a voltage at the source which reduces the gate drive current. The voltage is determined by Ldi/dt, but since di/dt is a function of drain current, the mathematical solution is complex. The MOSFET output capacitance also complicates the mathematics. And finally, MOSFETs have finite internal gate resistance which effectively adds to the resistance of the driving source, but the internal resistance is difficult to measure and, consequently, is not specified.

The resistive switching time variation versus gate resistance (Figure 9) shows how typical switching performance is affected by the parasitic circuit elements. If the parasitics were not present, the slope of the curves would maintain a value of unity regardless of the switching speed. The circuit used to obtain the data is constructed to minimize common inductance in the drain and gate circuit loops and is believed readily achievable with board mounted components. Most power electronic loads are inductive; the data in the figure is taken with a resistive load, which approximates an optimally snubbed inductive load. Power MOSFETs may be safely operated into an inductive load; however, snubbing reduces switching losses.



GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation



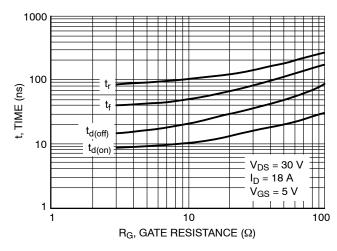


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

Figure 9. Resistive Switching Time Variation versus Gate Resistance

#### DRAIN-TO-SOURCE DIODE CHARACTERISTICS

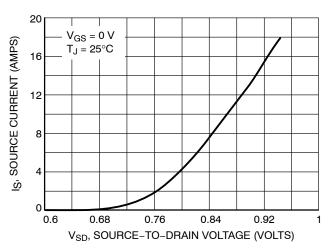


Figure 10. Diode Forward Voltage versus Current

#### SAFE OPERATING AREA

The Forward Biased Safe Operating Area curves define the maximum simultaneous drain-to-source voltage and drain current that a transistor can handle safely when it is forward biased. Curves are based upon maximum peak junction temperature and a case temperature (T<sub>C</sub>) of 25°C. Peak repetitive pulsed power limits are determined by using the thermal response data in conjunction with the procedures discussed in AN569, "Transient Thermal Resistance – General Data and Its Use."

Switching between the off-state and the on-state may traverse any load line provided neither rated peak current ( $I_{DM}$ ) nor rated voltage ( $V_{DSS}$ ) is exceeded and the transition time ( $t_p t_f$ ) do not exceed 10  $\mu$ s. In addition the total power averaged over a complete switching cycle must not exceed ( $T_{J(MAX)} - T_C$ )/( $R_{\theta JC}$ ).

A Power MOSFET designated E-FET can be safely used in switching circuits with unclamped inductive loads. For reliable operation, the stored energy from circuit inductance dissipated in the transistor while in avalanche must be less than the rated limit and adjusted for operating conditions differing from those specified. Although industry practice is to rate in terms of energy, avalanche energy capability is not a constant. The energy rating decreases non–linearly with an increase of peak current in avalanche and peak junction temperature.

Although many E–FETs can withstand the stress of drain–to–source avalanche at currents up to rated pulsed current ( $I_{DM}$ ), the energy rating is specified at rated continuous current ( $I_D$ ), in accordance with industry custom. The energy rating must be derated for temperature as shown in the accompanying graph (Figure 12). Maximum energy at currents below rated continuous  $I_D$  can safely be assumed to equal the values indicated.

#### SAFE OPERATING AREA

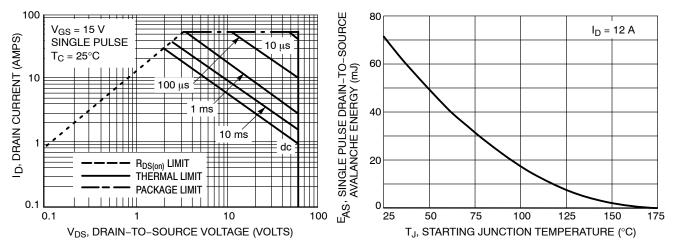


Figure 11. Maximum Rated Forward Biased Safe Operating Area

Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

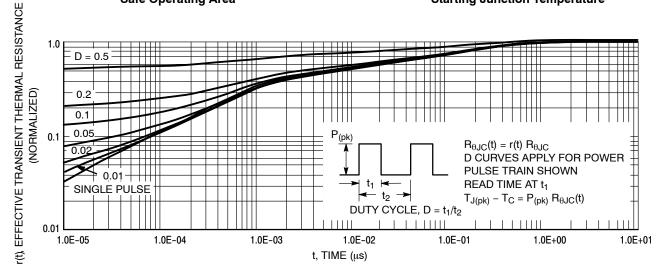


Figure 13. Thermal Response

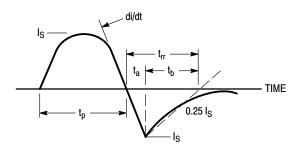


Figure 14. Diode Reverse Recovery Waveform

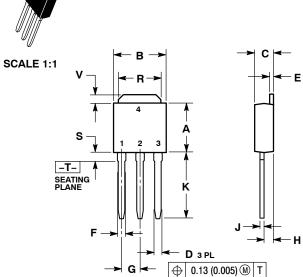
# MECHANICAL CASE OUTLINE

**PACKAGE DIMENSIONS** 





**DATE 15 DEC 2010** 



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

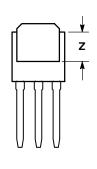
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

**EMITTER** 

COLLECTOR



#### NOTES:

- DIMENSIONING AND TOLERANCING PER
  ANSI V14 5M 1992
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

#### MARKING DIAGRAMS

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 3: PIN 1. ANODE

2. CATHODE

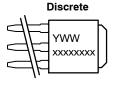
4. CATHODE

3 ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR





xxxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

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**DETAIL A** ROTATED 90° CW

# **DPAK (SINGLE GAUGE)** CASE 369C **ISSUE F**

**DATE 21 JUL 2015** 

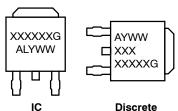
# NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

## **GENERIC MARKING DIAGRAM\***



XXXXXX = Device Code

= Assembly Location Α

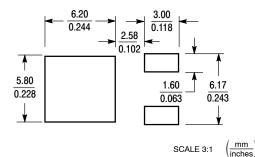
L = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

### SCALE 1:1 Α С -h3∙ В L3 z Ո DETAIL A Ш NOTE 7 C-**BOTTOM VIEW** b2 e SIDE VIEW | + 0.005 (0.13) M C **TOP VIEW** Z Ħ L2 GAUGE C SEATING **BOTTOM VIEW** Α1 ALTERNATE CONSTRUCTIONS

STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE PIN 1. BASE 2. COLLECTOR 3. EMITTER PIN 1. GATE 2. DRAIN PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3. GATE SOURCE 3. ANODE 4. CATHODE 4. COLLECTOR 4. DRAIN 4. ANODE 4. ANODE STYLE 6: STYLE 7: STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. GATE 2. COLLECTOR PIN 1. N/C 2. CATHODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3. GATE 4. MT2 3. EMITTER 4. COLLECTOR 3. ANODE 4. CATHODE 3. RESISTOR ADJUST 4. CATHODE 3. CATHODE 4. ANODE

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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